# 2SC5212

FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

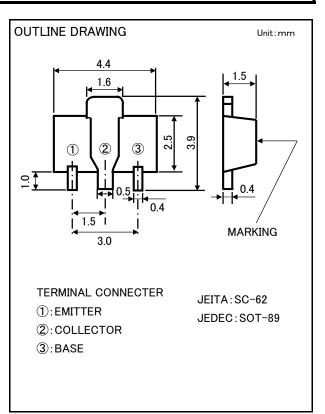
2SC5212 is a resin sealed silicon NPN epitaxial transistor. It designed with high collector current, small VCE(sat). Complementary with 2SA1946.

## FEATURE

- •Small package for easy mounting
- High collector current ICM=1000mA
- Low collector to emitter saturation voltage VCE(sat)=0.2V typ
- •Excellent linearity of DC forward current gain.
- High gain band with product fT=180MHz typ

## **APPLICATION**

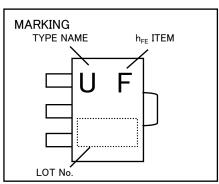
Small type motor drive, relay drive, power supply



## MAXIMUM RATINGS(Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base voltage	V <sub>CBO</sub>	25	V
Emitter to Base voltage	V <sub>EBO</sub>	4	V
Collector to Emitter voltage	V <sub>CEO</sub>	20	V
Collector current	Ic	700	mA
Peak collector current	I <sub>CM</sub>	1000	mA
Collector dissipation	P <sub>c</sub>	500	mW
Junction temperature	Tj	+150	°C
Storage temperature	$T_{stg}$	-55~+150	°C

## ELECTRICAL CHARACTERISTICS(Ta=25°C)



Parameter	Symbol	Test conditions		Limits		
Parameter	Symbol	l est conditions	Min	Тур	Max	Unit
C to B breakdown voltage	V(BR) <sub>CBO</sub>	$I_c=10 \mu$ A , $I_e=0$ mA	25	-	-	V
E to B breakdown voltage	V(BR) <sub>EBO</sub>	$I_{E}$ =10 $\mu$ A , $I_{C}$ =0mA	4	-	-	V
C to E breakdown voltage	V(BR) <sub>CEO</sub>	$I_{C}$ =100 $\mu$ A , R <sub>BE</sub> = $\infty$	20	-	-	V
Collector cut off current	Ісво	V <sub>CB</sub> =25V, I <sub>E</sub> =0mA	-	-	1	μA
Emitter cut off current	IEBO	$V_{EB}$ =2V, $I_{C}$ =0mA	-	-	1	μA
DC forward current gain *	hFE	V <sub>CE</sub> =4V, I <sub>C</sub> =100mA	150	-	800	_
C to E Saturation Voltage	VCE(sat)	$I_c$ =500mA , $I_B$ =25mA	-	0.2	0.5	V
Gain bandwidth product	fT	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	-	180	_	MHz

 $\%\colon$  It shows hFE classification at right table.

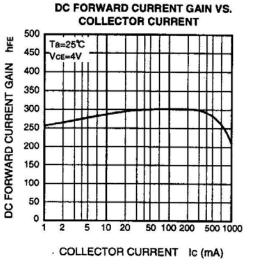
Item	E	F	G	
hFE	150~300	250~500	400~800	

## 2SC5212

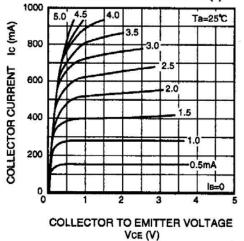
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#### COLLECTOR DISSIPATION VS AMBIENT TEMPERATURE 600 Pc(mW) 500 COLLECTOR DISSIPATION 400 300 200 100 0 0 25 50 75 100 125 150 AMBIENT TEMPERATURE Ta(°C)

TYPACAL CHARACTERISTICS



COMMON EMITTER OUTPUT (1)



 Ta=25°C

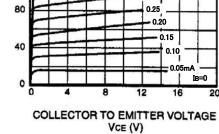
 160
 0.50

 120
 0.45

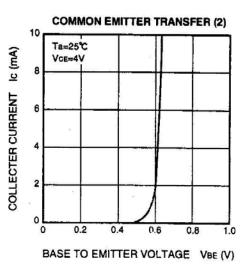
 120
 0.45

 0.35
 0.30

 80
 0.25



**COMMON EMITTER TRANSFER (1)** 1000 Ta=25°C Ic (mA) 900 VCE=4V 800 700 COLLECTOR CURRENT 600 500 400 300 200 100 0 0 0.2 0.4 0.6 0.8 1.0 BASE TO EMITTER VOLTAGE VBE (V)



COMMON EMITTER OUTPUT (2)

200

Ic (mA)

COLLECTOR CURRENT



6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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